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參考資料目錄:

- A. Journal Paper - SCI (期刊論文)
- B. Journal Paper - EI (期刊論文)
- C. Conference Paper (會議論文)
- D. Patent (專利)
- E. 執行研究計畫

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- A. Journal Paper - SCI (期刊論文)

- A1. Ming-Kwei Lee, **Chih-Feng Yen** and Shih-Hao Lin, "Electrical improvements of MOCVD-TiO₂ on (NH₄)₂S_x Treated InP by Post-Metallization Annealing," *J. Electrochem. Soc.*, Vol. 154, pp. G229, Oct. 2007. (SCI, Impact Factor 2.42, Material Science-coating & Films 1/18)
- A2. Ming-Kwei Lee, **Chih-Feng Yen** and Shi-Hao Lin, "Low Interface State Density of Liquid Phase Deposited SiO₂ Films on (NH₄)₂S_x Treated InP," *J. Electrochem. Soc.*, Vol. 154, pp. G235, Oct. 2007. (SCI, Impact Factor 2.42, Material Science-coating & Films 1/18)
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- A7. Ming-Kwei Lee and **Chih-Feng Yen**, “**Characterization of Fluorinated-SiO₂/PMA-treated TiO₂/(NH₄)₂S-treated GaAs MOS Structure**”, *J. Electrochem. Soc.*, Vol. 158, no. 8, G199-G202, 2011. (SCI, Impact Factor 2.42, Material Science-coating & Films 1/18)
- A8. Ming-Kwei Lee, **Chih-Feng Yen** and Sheng-Hsiung Yang, “Electrical Characteristics of Ultrathin Atomic Layer Deposited TiO₂ and Al₂O₃/TiO₂ Stacked Dielectrics on (NH₄)₂S_x-treated InP”, *IEEE Transactions on Electron Devices*. Vol. 58, no. 11, 3885-3889, 2011. (SCI, Impact Factor 2.255, ENGINEERING, ELECTRICAL & ELECTRONIC, 32/247)
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- A19. Ming-Kwei Lee and **Chih-Feng Yen***(通訊作者), “Electrical Characteristics of TiO₂/Al₂O₃/InP Capacitor after Removal of Native Oxides by Atomic Layer Deposited Al₂O₃ Self-cleaning and (NH₄)₂S Treatments”, *Thin solid films*. Vol. 595, 12-16, Oct. 2015. (SCI, Impact Factor 1.72, Material Science-coating & Films 5/17)
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- A21. **Chih-Feng Yen**, Min-Yen Yeh, Kwok-Keung Chong, Chun-Fa Hsu and Ming-Kwei Lee, “InP MOS Capacitor and E-mode N-channel FET with ALD Al₂O₃ Based High-k Dielectric”, *Applied Physics A: Materials Science & Processing*. Vol. 122, Issue 7, 683, 2016. (SCI, Impact Factor 1.63, PHYSICS, APPLIED 48/125)
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B. Journal Paper - EI (期刊論文)

- B1. Ming-Kwei Lee, Nai-Roug Cheng, Cho-Han Fan and **Chih-Feng Yen**, “Efficiency Improvement of Solar Cell with ZnO Nanotip Array Prepared by Aqueous Solution Deposition”, *Advanced Materials Research*, Vol. 339 (2011) pp. 283-286. (EI)
- B2. Ming Kwei Lee, **Chih Feng Yen**, Sheng Hsiung Yang, Jung Chan Lee, Chi Hsuan Cheng and Wei Hau Cheng, “Electrical Characteristics of Stacked Titanium Oxide/Aluminum Oxide by Atomic Layer Deposition on (NH₄)₂S-Treated GaAs”, *Advanced Materials Research*, vol. 516-517, 1945-1948, 2012. (EI)

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C. Conference Paper (會議論文)

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- C6. Ming-Kwei Lee, Nai-Roug Cheng, Cho-Han Fan and **Chih-Feng Yen**, “Orientation of ZnO Nanotip Array Controlled by Thickness of ZnO Seed Layer”, 2011 International Conference on Advanced Engineering Materials and Technology (AEMT 2011), Sanya, China, July 29-31, 2011.
- C7. Ming-Kwei Lee, Nai-Roug Cheng, Cho-Han Fan and **Chih-Feng Yen**, “Efficiency Improvement of Solar Cell with ZnO Nanotip Array Prepared by Aqueous Solution Deposition”, 2011 International Conference on Materials and Products Manufacturing Technology, October 28-30, Chengdu, China.
- C8. Ming-Kwei Lee, Nai-Roug Cheng and **Chih-Feng Yen**, “Density of ZnO Nanotip Array Controlled by Thickness of ZnO Seed Layer”, 2nd International Advances in Applied Physics and Materials Science (APMAS 2012), from 26 to 29 April 2012 in Antalya, Turkey.
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- C17. **Chih-Feng Yen^{a)}**, Chong-Yi Lee, Min Yen Yeh, Kwok-Keung Chong, Chyi-Da Yang, Rwei-Jun Hong and Shan-Hsiung Li, “The study of hafnium dioxide on Si by non-vacuum deposition process”, 2018 International Conference on “Physics and Mechanics of New Materials and Their Applications” (PHENMA 2018), pp. 44, Jabalpur, India, October 14-16, 2017.
- C18. **Chih-Feng Yen^{a)}**, Chong-Yi Lee, Min Yen Yeh, Kwok-Keung Chong, Chyi-Da Yang, Rwei-Jun Hong and Shan-Hsiung Li, “The study of hafnium dioxide on Si by non-vacuum deposition process”, 2018 International Conference on “Physics and Mechanics of New Materials and Their Applications” (PHENMA 2018), pp. 98, Busan, South Korea, August 9-11, 2018.
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- C22. **Chih-Feng Yen***, Tzu-Yang Shen, Shan-Hsiung Li and Ruei-Jun Hong, “Si MOS capacitor with O₂ annealed ZrO₂/Al₂O₃ gate oxide prepared by liquid phase deposition”, The 597th International Conference on Science, Engineering & Technology, pp. 1, Auckland, New Zealand, March 5-6, 2020.
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- C32. **Chih-Feng Yen***, Shen-Hao Tsao, Yu-Ya Huang, “Zirconium oxide dielectric layer: preparation and characterization with various volumes of acetylacetone”, 5th IEEE International Conference on Knowledge Innovation and Invention 2022 (IEEE ICKII 2022), Hualien, Taiwan, July 22-24, 2022.
- C33. **Chih-Feng Yen***, Yu-Ya Huang, and Shen-Hao Tsao, “Influence of Y₂O₃ doped HfO₂ high-k films on the electrical properties of MOS and MIM devices”, 5th IEEE International Conference on Knowledge Innovation and Invention 2022 (IEEE ICKII 2022), Hualien, Taiwan, July 22-24, 2022.

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- C34. **顏志峰**、王美玲、廖怡婷、陳泊勳、姚文洋，“利用液相沉積法製備二氧化矽抗反射層對於染料敏化太陽電池之影響”，2017 第十五屆微電子技術發展與應用研討會，高雄，台灣，13 頁，中華民國一百零六年五月十九日
- C35. **顏志峰**、陳政成、王泓錡、鄭名軒、徐元伯，“液相沉積法製備 TiO₂ 薄膜應用於 DSSC 阻隔層”，2017 第十五屆微電子技術發展與應用研討會，高雄，台灣，63 頁，中華民國一百零六年五月十九日
- C36. **顏志峰**、邱嘉輝，“銅線製程對鉛墊受損鉛線參數研究”，2018 第十六屆微電子技術發展與應用研討會，高雄，台灣，47-48 頁，中華民國一百零七年五月二十五日
- C37. **Chih-Feng Yen^{a)}**, Yi-Fan Lu, Shun-Ming Hu, Cheng-Hsien Tsai, Ming-Chih Tsai, “Investigation of magnesium oxide films on silicon substrate with liquid phase deposition,” 2019 17th conference on microelectronics and applications, pp. 23, Kaohsiung, Taiwan, May 24, 2019.
- C38. **Chih-Feng Yen^{a)}**, Wen-Feng Fan, Shen-Ming Hu, and Yi-Fan Lu, "Research on improving electrical characteristics of Y₂O₃/Si MOS annealing environment", 2021 19th Conference on Microelectronics Technology & Application, pp.40, Kaohsiung, ROC, May 21, 2021.
- C39. **Chih-Feng Yen^{a)}**, Shen-Ming Hu, Wen-Feng Fan, and Yi-Fan Lu, “Study on the structure of liquid-deposited ZnO/p-Si MOS prepared by deposition different times”, 2021 19th Conference on Microelectronics Technology & Application, pp.21, Kaohsiung, ROC, May 21, 2021.
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- C41. Chih-Feng Yen^{a)}, An-Zhe Zheng, Yu-De Lin, and Jun-Wei Xu, "Research on Preparation of Zinc Oxide Film on Silicon Substrate by Sol-Gel Method", 2021 19th Conference on Microelectronics Technology & Application, pp.56, Kaohsiung, ROC, May 21, 2021.
- C42. Chih-Feng Yen^{a)}, and You-Ming Liu, "Research on the warpage change of the small out-line package by the shadow moiré", 2021 19th Conference on Microelectronics Technology & Application, pp.1, Kaohsiung, ROC, May 21, 2021.
- C43. 顏志峰*、柯智懷，"以溶膠凝膠法製備新穎氧化鋁/氧化鋅複合材料於矽基板之研究"，2022 年功能性材料研討會暨科技部專題研究計畫成果發表會，台南，台灣，149 頁，中華民國一百一十一年六月十日
- C44. 顏志峰*、何家豪，"晶背研磨介紹及刻痕改善"，2022 第二十屆微電子技術發展與應用研討會，高雄，台灣，1 頁，中華民國一百一十一年五月二十日
- C45. 顏志峰*、李晉璋，"添加微量元素對無鉛錫球與鍍錫基板結合能力之評估"，2022 第二十屆微電子技術發展與應用研討會，高雄，台灣，6 頁，中華民國一百一十一年五月二十日
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D. Patent (專利)

- D1. 李明達、黃俊杰和顏志峰，"一種高介電常數與低漏電流磷化銦金氧半電容的製作方法"，中華民國，發明專利第 I 249841 號
- D2. 李明達、黃俊杰、顏志峰和吳宗訓，"Method for making a metal oxide semiconductor device"，美國，發明專利，**US 7,341,960 B2**

E. 執行研究計畫

- E1. 以超薄 LPD-SiON/非真空式 ALD-TiO₂ 為閘極氧化層之增強型 N 通道磷化銦電晶體製作，104-2221-E-022 -016-
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